

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF314** is Designed for Class C Power Amplifier Applications up to 200 MHz.

FEATURES:

- $P_G = 10$ dB min. at 30 W/ 150 MHz
- Withstands 30:1 Load VSWR
- *Omnigold™* Metalization System

MAXIMUM RATINGS

I_C	3.4 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.13 °C/W

PACKAGE STYLE .380 4L FLG																											
<table border="1"> <thead> <tr> <th>MINIMUM Dimensions</th> <th>MAXIMUM Dimensions</th> </tr> </thead> <tbody> <tr> <td>2.05/16.98</td> <td>2.05/16.98</td> </tr> <tr> <td>2.05/16.94</td> <td>2.05/16.94</td> </tr> <tr> <td>1.95/16.98</td> <td>2.05/16.94</td> </tr> <tr> <td>3.05/16.94</td> <td>5.05/16.95</td> </tr> <tr> <td>—</td> <td>3.05/16.94</td> </tr> <tr> <td>3.05/16.94</td> <td>3.05/16.94</td> </tr> <tr> <td>—</td> <td>3.05/16.94</td> </tr> <tr> <td>1.95/16.95</td> <td>2.05/16.95</td> </tr> <tr> <td>2.05/16.95</td> <td>2.05/16.95</td> </tr> <tr> <td>1.95/16.95</td> <td>2.05/16.95</td> </tr> <tr> <td>—</td> <td>2.05/16.95</td> </tr> <tr> <td>2.05/16.95</td> <td>2.05/16.95</td> </tr> </tbody> </table>		MINIMUM Dimensions	MAXIMUM Dimensions	2.05/16.98	2.05/16.98	2.05/16.94	2.05/16.94	1.95/16.98	2.05/16.94	3.05/16.94	5.05/16.95	—	3.05/16.94	3.05/16.94	3.05/16.94	—	3.05/16.94	1.95/16.95	2.05/16.95	2.05/16.95	2.05/16.95	1.95/16.95	2.05/16.95	—	2.05/16.95	2.05/16.95	2.05/16.95
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ORDER CODE: ASI10872																											

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 30$ mA	35			V
BV_{CES}	$I_C = 30$ mA	65			V
BV_{EBO}	$I_E = 3.0$ mA	4.0			V
I_{CBO}	$V_E = 30$ V			3.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.5$ A	20		80	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz		30	40	pF
P_G η_c ψ	$V_{CC} = 28$ V $P_{OUT} = 30$ W $f = 150$ MHz	10 50	13.5		dB %
		30:1 all phase angles, no degradation in output.			

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